Intel and Micron Receive Most Innovative Flash Memory Technology Award at 2011 Flash Memory Summit

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SANTA CLARA, Calif. and BOISE, Idaho, Aug. 11, 2011 (GLOBE NEWSWIRE) -- Intel Corporation (Nasdaq:INTC) and Micron Technology, Inc. (Nasdaq:MU), received the Most Innovative Flash Memory Technology award Aug. 10 at the 2011 Flash Memory Summit for the companies' industry-leading 20 nanometer (nm) NAND Flash memory process technology.

The 20nm 8 gigabyte (GB) NAND device from Intel and Micron delivers the highest capacity in the smallest form factor. Manufactured by IM Flash Technologies, the NAND flash joint venture from Intel and Micron, the new device is a breakthrough in NAND process and technology design, further extending the companies' lithography leadership.

Shrinking NAND lithography to this technology node is the most cost-effective method for increasing NAND output to date, providing approximately 50 percent more gigabyte capacity than current technology. The new 20nm process technology also helps further the companies' dual goal to enable instant, affordable access to the world's information.

"The growth in storage all the way from the data center to full-featured smartphones and tablets is creating new demands for NAND flash technology, especially greater capacity in smaller designs," said Glen Hawk, vice president of Micron's NAND Solutions Group. "Micron is proud of the industry-leading technology we have developed with Intel, and we're pleased to have this technology honored by the Flash Memory Summit."

"NAND silicon process and die level innovation is foundational for the flash memory industry to provide compelling end solutions like solid-state drives," said Tom Rampone, Intel vice president and general manager of the Intel Non-Volatile Memory Solutions Group. "We are pleased that the Flash Memory Summit continues to recognize the innovation and success that Intel and Micron are achieving together."

Additionally, the new 20nm 8GB device measures just 118mm^2 and enables a 30 to 40 percent reduction in board space (depending on package type) compared to existing 25nm 8GB NAND devices. A reduction in the flash storage layout provides greater system level efficiency as it enables tablet and smartphone manufacturers to use the extra space for end-product improvements such as a bigger battery, larger screen or adding another chip to handle new features.

Flash Memory Summit is the only conference dedicated entirely to flash memory and its applications. It is intended for system designers, analysts, hardware and software engineers, product marketing and marketing communications specialists, and engineering and marketing managers. It features forums, half-day tutorials, paper and panel sessions, and expert tables. Subjects include harsh environments, laptops, enterprise storage system applications, consumer products, performance, product design, caching methods, design methods, software, new technologies, market research, testing and reliability, and security. The Summit also includes exhibits of the latest products and product awards. For more information, visit www.flashmemorysummit.com.

Intel (Nasdaq:INTC) is a world leader in computing innovation. The company designs and builds the essential technologies that serve as the foundation for the world's computing devices. Additional information about Intel is available at newsroom.intel.com and blogs.intel.com.

Micron Technology, Inc., is one of the world's leading providers of advanced semiconductor solutions. Through its worldwide operations, Micron manufactures and markets a full range of DRAM, NAND and NOR flash memory, as well as other innovative memory technologies, packaging solutions and semiconductor systems for use in leading-edge computing, consumer, networking, embedded and mobile products. Micron's common stock is traded on the NASDAQ under the MU symbol. To learn more about Micron Technology, Inc., visit www.micron.com.

The Micron Technology, Inc. logo is available at http://www.globenewswire.com/newsroom/prs/?pkgid=6950

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CONTACT: Deb Paquin

Intel NVM Solutions Group

916-984-1921

debpaquin@strategiccom.biz

Daniel Francisco

Micron Technology, Inc.

208-368-5584

dfrancisco@micron.com